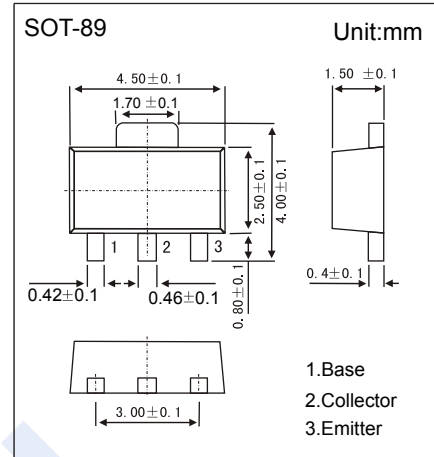


PNP Transistors

2SA1384

■ Features

- Collector Current Capability $I_C = -0.1A$
- Collector Emitter Voltage $V_{CE0} = -300V$
- Complementary to 2SC3515



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-300	V
Collector - Emitter Voltage	V_{CEO}	-300	
Emitter - Base Voltage	V_{EBO}	-8	
Collector Current - Continuous	I_C	-100	mA
Base Current	I_B	-20	
Collector Power Dissipation (Note.1)	P_C	500	mW
		1	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

Note.1: 2SA1384 mounted on ceramic substrate (250mm²X0.8mm^t)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu A, I_E = 0$	-300			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 mA, I_B = 0$	-300			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_C = 0$	-8			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -300 V, I_E = 0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -8 V, I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20 mA, I_B = -2 mA$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20 mA, I_B = -2 mA$			-1	
DC current gain	h_{FE}	$V_{CE} = -10V, I_C = -20mA$	30		150	
		$V_{CE} = -10V, I_C = -1mA$	20			
Collector output capacitance	C_{ob}	$V_{CB} = -20V, I_E = 0, f = 1MHz$			8	pF
Transition frequency	f_T	$V_{CE} = -10V, I_C = -20mA$	50			MHz

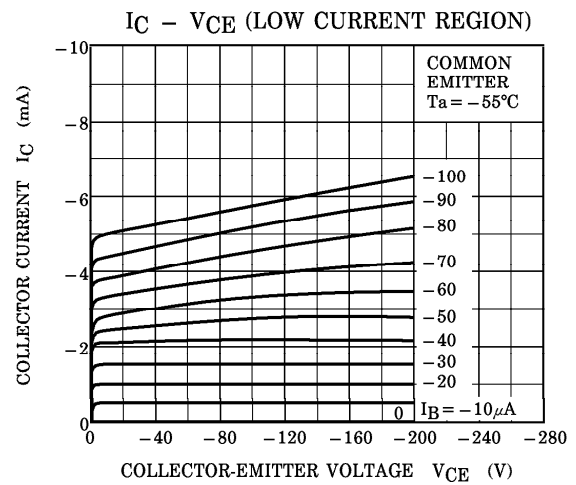
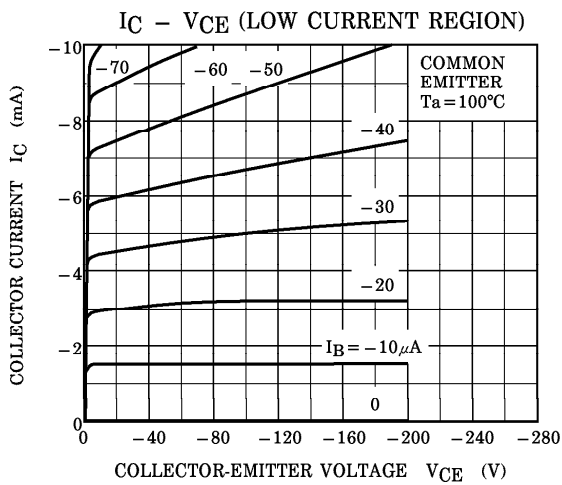
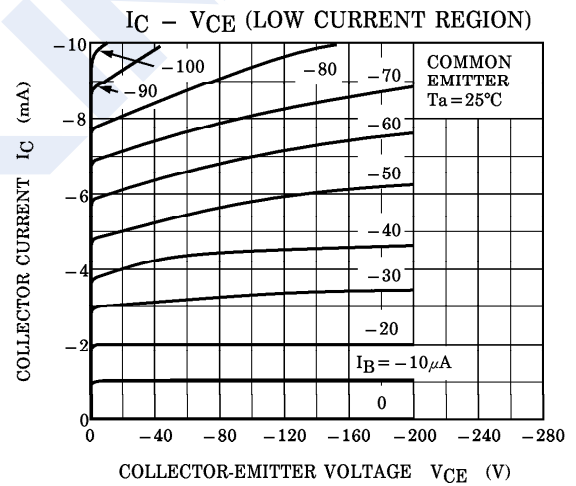
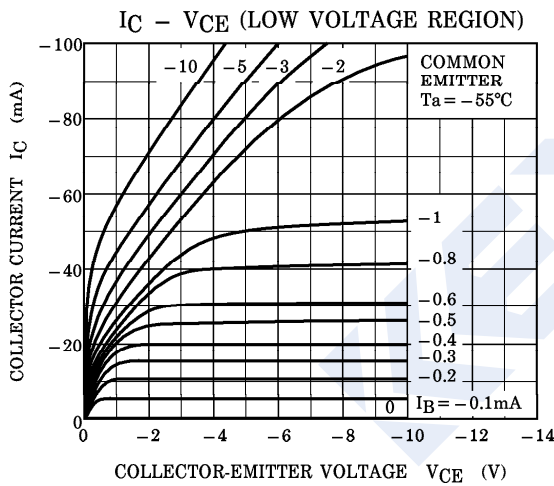
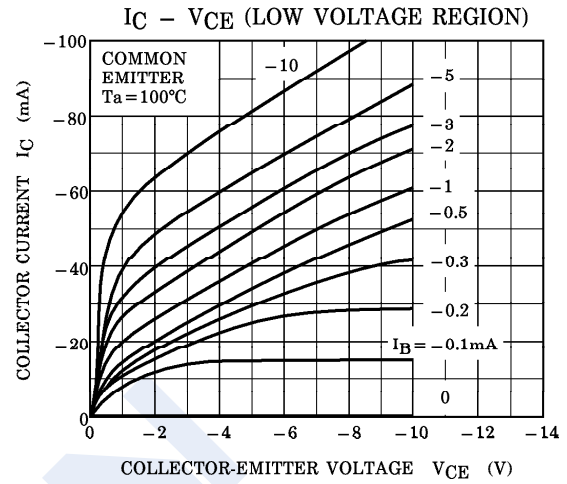
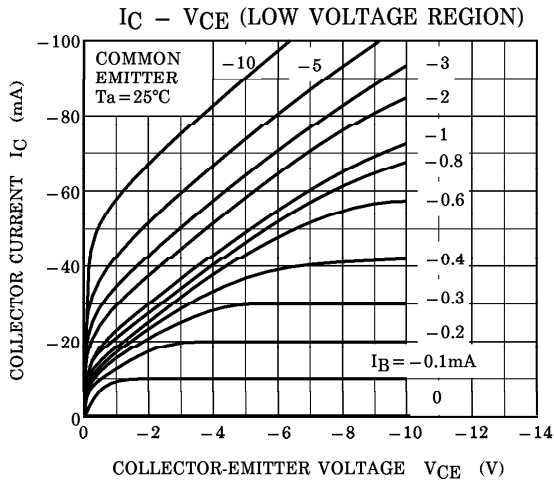
■ Classification of $h_{fe}(1)$

Type	2SA1384-R	2SA1384-O
Range	30-90	50-150
Marking	JR	JO

PNP Transistors

2SA1384

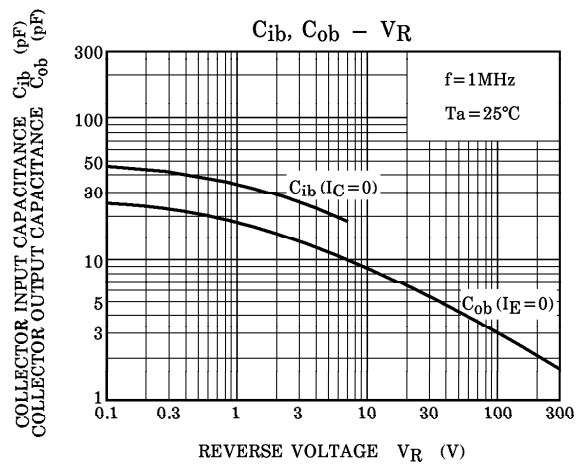
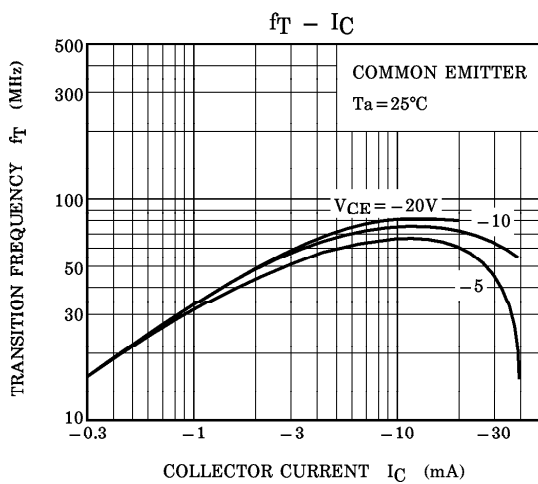
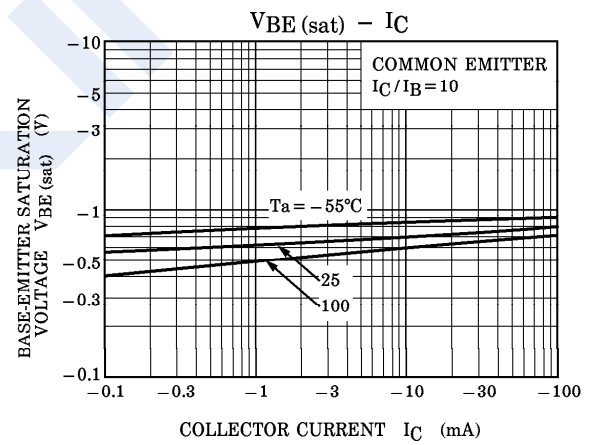
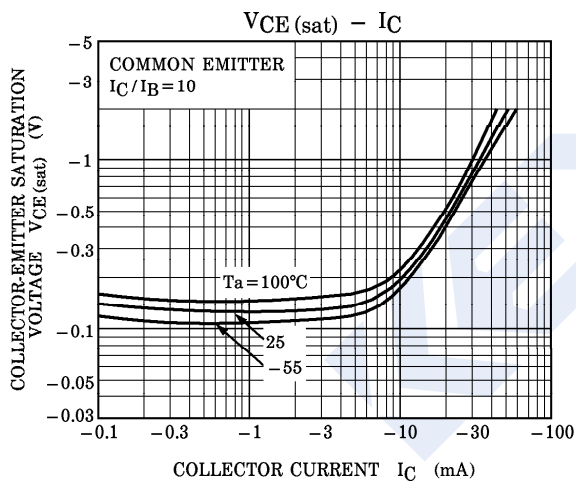
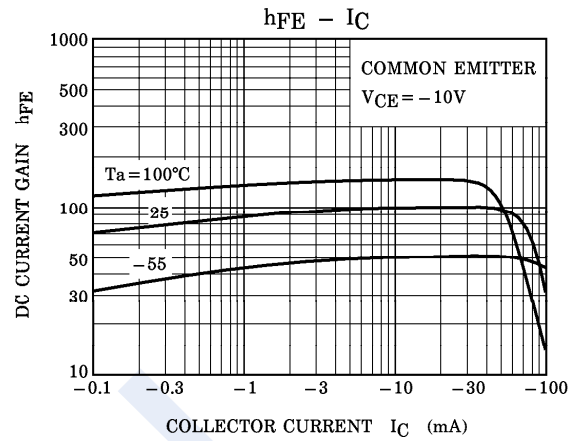
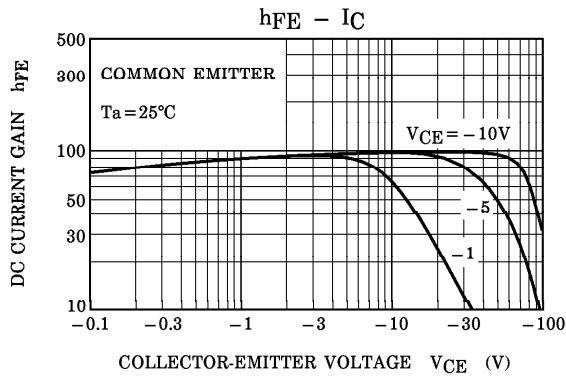
■ Typical Characteristics



PNP Transistors

2SA1384

■ Typical Characteristics



PNP Transistors

2SA1384

■ Typical Characteristics

